

CEM3307-VB Datasheet Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY							
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A) ^{d, e}	Q _g (Typ.)				
- 30	0.035 at V _{GS} = - 10 V	- 7.3	17 nC				
- 30	0.045 at V _{GS} = - 4.5 V	- 6.3	17110				

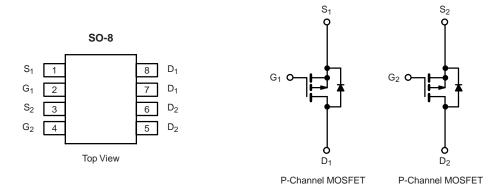
FEATURES

- · Halogen-free
- Trench Power MOSFET
- 100 % UIS Tested



APPLICATIONS

· Load Switches



Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 30	V	
Gate-Source Voltage	V _{GS}	± 20	V	
	T _C = 25 °C		- 7.3 ^e	
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C]	- 7.0 ^e	
Continuous Diam Current (1) = 130 °C)	T _A = 25 °C	I _D	- 7.3 ^{a, b}	
	T _A = 70 °C		- 5.9 ^{a, b}	Α
Pulsed Drain Current	I _{DM}	- 32 ^e	A	
0 1 0 0 0 1	T _C = 25 °C	_	- 4.1	
Continuous Source-Drain Diode Current	T _A = 25 °C	ls -	- 2.0 ^{a, b}	
Avalanche Current	L = 0.1 mH	I _{AS}	- 20	
Single-Pulse Avalanche Energy	L = 0.1 mm	E _{AS}	20	mJ
	T _C = 25 °C		5.0	
Mayimum Dawar Dissination	T _C = 70 °C	P _D	3.2	W
Maximum Power Dissipation	T _A = 25 °C		2.5 ^{a, b}	VV
	T _A = 70 °C	1	1.6 ^{a, b}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{a, c}	t ≤ 10 s	R _{thJA}	38	50	°C/W	
Maximum Junction-to-Foot	Steady State	R_{thJF}	20	25] -C/W	

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. t = 10 s.
- c. Maximum under Steady State conditions is 85 °C/W.
- d. Based on $T_C = 25 \, ^{\circ}C$.
- e. Limited by package.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	-						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	In = - 250 µA		- 31		m\//0/	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μA		4.5		mV/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zana Cata Valtana Busin Comment	1	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	- 1		- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 5	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 30			Α	
Davis Course Co Otata Basista and	_	V _{GS} = - 10 V, I _D = - 6.3 A		0.035			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 6.2 A		0.040		Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 6.1 A		23		S	
Dynamic ^b							
Input Capacitance	C _{iss}			1350		pF	
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		215			
Reverse Transfer Capacitance	C _{rss}			185			
Total Gate Charge	0	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -6.1 \text{ A}$		32	50		
	Q_g			15	25	200	
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -6.1 \text{ A}$		4		nC	
Gate-Drain Charge	Q_{gd}			7.5			
Gate Resistance	R_g	f = 1 MHz		5.8		Ω	
Turn-On Delay Time	t _{d(on)}			10	15		
Rise Time	t _r	$V_{DD} = -15 \text{ V}, R_{L} = 15 \Omega$		8	15		
Turn-Off DelayTime	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 10 V, R_g = 1 Ω		45	70		
Fall Time	t _f			12	25	20	
Turn-On Delay Time	t _{d(on)}			42	70	ns	
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		35	60		
Turn-Off DelayTime	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		40	70		
Fall Time	t _f]		16	30		
Drain-Source Body Diode Characterist	ics				•		
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 4.1	۸	
Pulse Diode Forward Current	I _{SM}				- 32	Α	
Body Diode Voltage	V _{SD}	I _S = - 2 A, V _{GS} = 0 V		- 0.75	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			34	60	ns	
Body Diode Reverse Recovery Charge Q _{rr}		1 2 A d1/d+ 100 A/va T 25 °C		22	40	nC	
Reverse Recovery Fall Time	t _a	$I_F = -2 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		11			
Reverse Recovery Rise Time		t _b		23	İ	ns	

Notes:

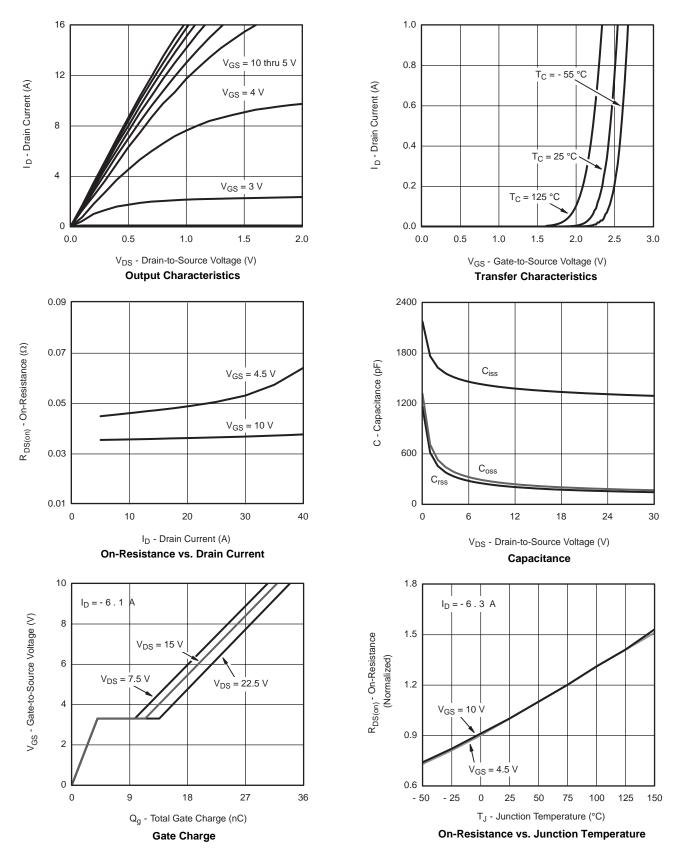
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

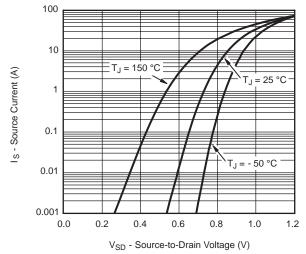


TYPICAL CHARACTERISTICS 25 C, unless otherwise noted

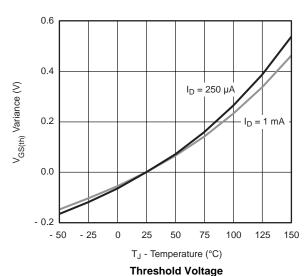




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Source-Drain Diode Forward Voltage



I_D = -6.3 A 0.08 $R_{DS(on)}$ - On-Resistance (Ω) 0.06 T_J = 125 °C 0.04 0.02 T_J = 25 °C 0.00

0.10

0

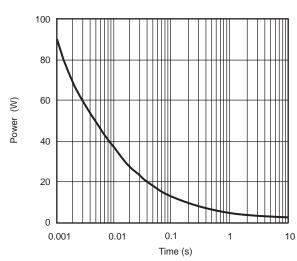
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V_{GS} - Gate-to-Source Voltage (V) On-Resistance vs. Gate-to-Source Voltage

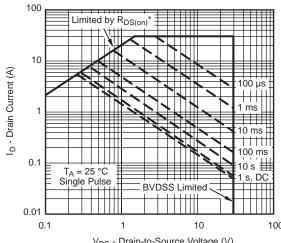
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8

10



Single Pulse Power, Junction-to-Ambient



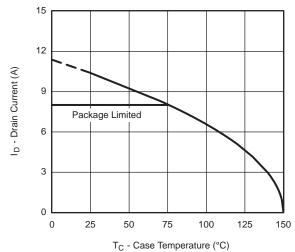
V_{DS} - Drain-to-Source Voltage (V)

Safe Operating Area

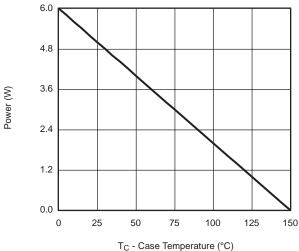
^{*} V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

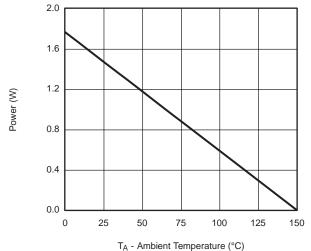


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







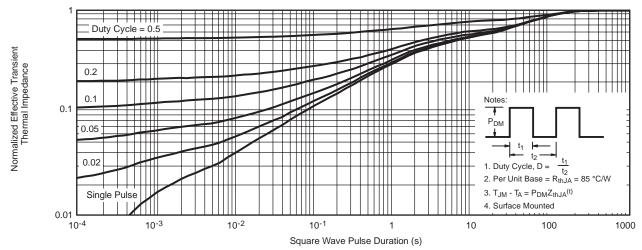


Power, Junction-to-Foot Power Derating, Junction-to-Ambient

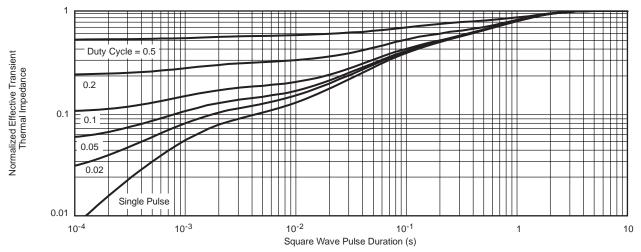
^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

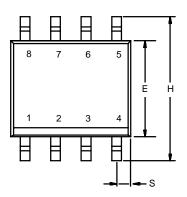


Normalized Thermal Transient Impedance, Junction-to-Foot

服务热线:400-655-8788 6



SOIC (NARROW): 8-LEADJEDEC Part Number: MS-012







	MILLIMETERS		INCHES			
DIM	Min	Max	Min	Max		
А	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
FCN: C-06527-Rev 11-Sen-06						

ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498

服务热线:400-655-8788 7



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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